Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S26	559	semiconductor and mask$4 and (sio or oxide) and (sion or oxynitride) and (sin or nitride) and @ad<"19951230" and photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:06
S48	559	semiconductor and mask$5 and (sio or oxide) and (sion or oxynitride) and (sin or nitride) and @ad<"19951230" and photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:10
S49	14	semiconductor and (((anti-reflect$6 or antireflect$6 or ARC) with (SION or SiNO or oxynitride)) same (photoresist or resist)) and @ad<"19951230" and photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:12
S28	14	semiconductor and (((anti-reflect$5 or antireflect$5 or ARC) with (SION or SiNO or oxynitride)) same (photoresist or resist)) and @ad<"19951230" and photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:12
S29	27	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) with (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:16
S50	27	semiconductor and ((anti-reflect$6 or antireflect$5 or ARC) with (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:17
S52	13	semiconductor and ((anti-reflect$6 or antireflect$5 or ARC) with (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist not S51	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:18
S51	14	semiconductor and (((anti-reflect$5 or antireflect$5 or ARC) with (SION or SiNO or oxynitride)) same (photoresist or resist)) and @ad<"19951230" and photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:18
S32	23	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist not (S29 or S30)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:18

S30	13	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) with (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist not S28	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:18
S57	23	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist not (S53 or S54)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:19
S56	36	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist not S51	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:19
S55	23	semiconductor and ((anti-reflect$6 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist not (S53 or S54)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:19
S54	13	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) with (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist not S51	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:19
S53	27	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) with (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:19
S40	8	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" not (S28 or S29 or S30 or S31 or S32)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 19:19
S58	8	semiconductor and ((anti-reflect$6 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" not (S51 or S53 or S54 or S56 or S57)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 19:20

S41	18	(semiconductor or substrate) and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist or photolithograph$6 or lithograph$6) and @ad<"19951230" not (S28 or S29 or S30 or S31 or S32)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 19:20
S59	18	(semiconductor or substrate) and ((anti-reflect$6 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist or photolithograph$6 or lithograph$6) and @ad<"19951230" not (S51 or S53 or S54 or S56 or S57)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 19:22
S62	36	semiconductor and ((anti-reflect$6 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist not S51	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:26
S61	10	(semiconductor or substrate) and ((anti-reflect$6 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist or photolithograph$6 or lithograph$6) and @ad<"19951230" not (S51 or S53 or S54 or S56 or S57 or S60)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 19:26
S60	8	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" not (S51 or S53 or S54 or S56 or S57)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 19:26
S42	10	(semiconductor or substrate) and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist or photolithograph$6 or lithograph$6) and @ad<"19951230" not (S28 or S29 or S30 or S31 or S32 or S40)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 19:26
S31	36	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist) and @ad<"19951230" and photoresist not S28	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:26

S63	60	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (mask$5) and @ad<"19951230"	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:33
S65	10	(semiconductor or substrate) and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist or photolithograph$6 or lithograph$6) and @ad<"19951230" not (S51 or S53 or S54 or S56 or S57 or S60)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 19:50
S64	18	(semiconductor or substrate) and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (photoresist or resist or photolithograph$6 or lithograph$6) and @ad<"19951230" not (S51 or S53 or S54 or S56 or S57)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 19:50
S44	3	semiconductor and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (mask$5) and @ad<"19951230" not (S28 or S29 or S30 or S31 or S32 or S40 or S41 or S42)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:50
S67	48	(semiconductor or substrate) and ((anti-reflect$6 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and @ad<"19951230" not (S51 or S53 or S54 or S56 or S57 or S60)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 19:51
S66	3	semiconductor and ((anti-reflect$6 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and (mask$5) and @ad<"19951230" not (S51 or S53 or S54 or S56 or S57 or S60 or S64 or S65)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/12/02 19:51
S46	48	(semiconductor or substrate) and ((anti-reflect$5 or antireflect$5 or ARC) same (SION or SiNO or oxynitride)) and @ad<"19951230" not (S28 or S29 or S30 or S31 or S32 or S40)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/02 19:51